



BUV24

NPN Silicon Low Frequency High Power



Switching Transistor

Features:

1. Heavy working current.Good temperature stability.Excellent thermal fatigue capability.
2. Good Switching Characteristic.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Total Dissipation	P_{tot}	W	250	$T_c=25^\circ\text{C}$
Max. Collector Current	I_{CM}	A	20	
Junction Temperature	T_{jm}	$^\circ\text{C}$	175	
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	V	450	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	400	$I_c=10\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	V	7	$I_E=1\text{mA}$
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.6	$I_c=6\text{A}, I_B=1.2\text{A}$
Collector-Emitter Laekage Current	I_{CEO}	mA	3.0	$V_{CE}=300\text{V}$
Emitter-Base Laekage Current	I_{EBO}	mA	1.0	$V_{EB}=7\text{V}$
DC Current Gain	h_{FE}		15~60	$V_{CE}= 4\text{V}, I_c=6\text{A}$
Transition frequency	f_T	MHz	8	$V_{CE}= 15\text{V}, I_c=2\text{A}, f=4\text{MHz}$
Rise Time	t_r	us	1.6	$V_{CE}= 120\text{V}, I_c=12\text{A}, I_{B1}=2.4\text{A}, I_{B2}=-2.4\text{A}$
Storage Time	t_s	us	2.3	
Fall Time	t_f	us	1.4	

Outline and Dimensions: